



University of
Massachusetts
Amherst

ECE124
Intro-Digital and Computer Sys

Chapter 7

Memory and Programmable Logic

Memories

■ How is memory used in computers?

- Memory hierarchy (next slide)

■ What differentiates various types of memories?

- Technology: magnetic, charge, capacitance, resistance, fuse
- Access Flexibility: random (access anything), sequential (access in order)
 - » Random Access Memory (RAM) vs. Sequential Access Memory (SAM)
 - » USB memory vs. Magnetic type memory
 - » Access/Cycle Time: time required to complete a read/write operation
- Access Options (Memory function): Write (i.e. store) and read (i.e. retrieve), or read only
 - » Read-Write Memory (RWM) vs. ROM (Read-Only Memory)
- Volatility: non-volatile or volatile (does or does not retain data on power-down)
- Capacity: amount of data that can be stored—typically expressed in bytes
 - » Word Size: # bits stored or retrieved upon access

■ We'll consider two conventional memories

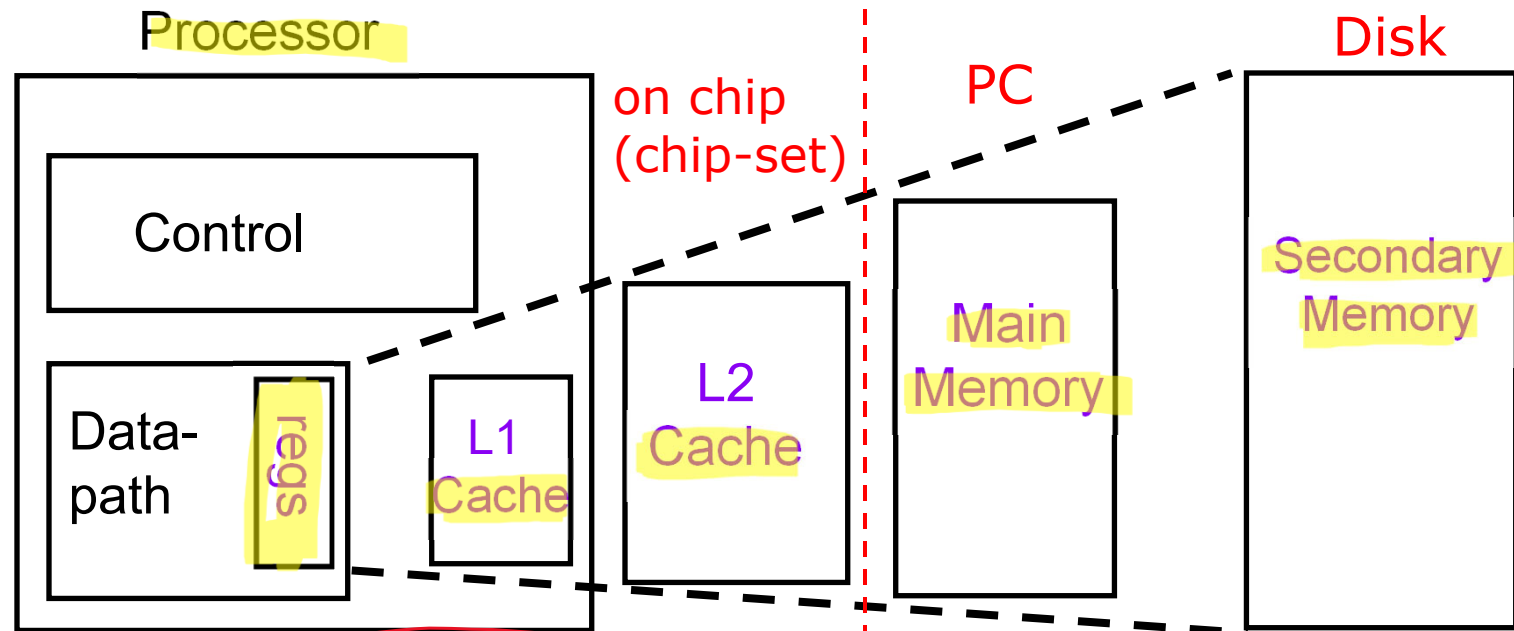
- Random-Access Memory (RAM)
- Read-Only Memory (ROM)

■ Is memory combinational or sequential logic?

- RAM: array of binary storage elements like sequential, but not clocked (latch)
- ROM: combinational (decoder + OR gates)

AND NAND gate

Memory Hierarchy



Speed (ns):	0.1ns	0.2ns	1ns	6ns	3,000,000ns
Size (MB):	0.00	0.5	2-6	4,000-8,000+	500,000+
Cost (\$/MB):	--	--	\$1	\$0.004	\$0.00001
Technology:	Regs	SRAM	SRAM	DRAM	Disk

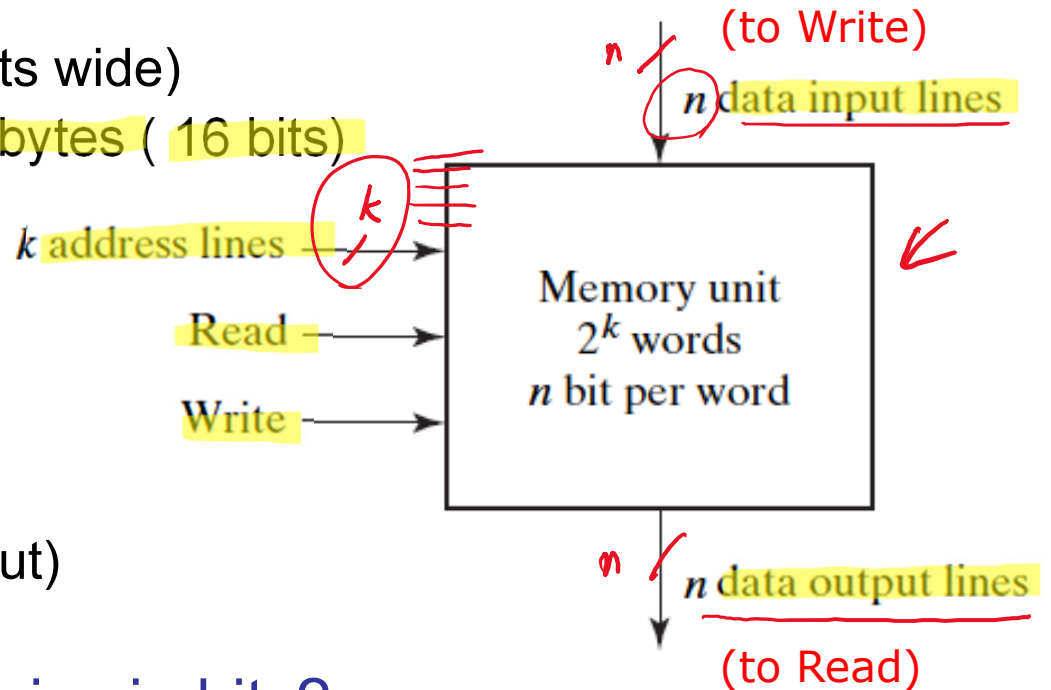
Random-access Memory (RAM)

Memory terminology:

- Smallest unit is "word" (n bits wide)
- 1 byte is 8 bits, 1 word is 2 bytes (16 bits)
- Identified by "address"

Block diagram:

- k address lines $k=10$
 - » At most 2^k words storage
- n data lines (input and output)
 $n=16$



What is the total memory size in bits?

- Size = $2^k \times n$ bits
 $= 2^{10} \times 16 \text{ bit} = 1024 \times 16 \text{ bit}$

Example:

- 1024-bit memory with 16-bit words
- How many address lines? 10 address line

$$1024 = 2^{10}$$

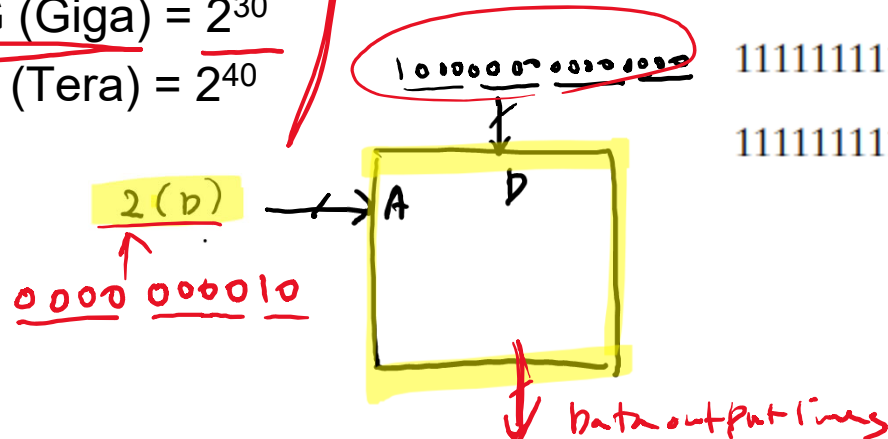
Memory Layout

■ Example: 1024x16 RAM

- 1024 16-bit words
- 10 bits identify address (or "location") of word
- 16 bit word stored at each location

■ Remember:

- k (Kilo) = 2^{10}
- M (Mega) = 2^{20}
- G (Giga) = 2^{30}
- T (Tera) = 2^{40}



10-bit address lines
Memory address

16-bit data line

Binary	decimal	Memory content
<u>0000000000</u>	0	<u>1011010101011101</u>
0000000001	1	1010101110001001
<u>0000000010</u>	2	0000110101000110
<u>2(D)</u>		<u>1000000000000000</u>
	⋮	⋮
1111111101	1021	1001110100010100
1111111110	1022	0000110100011110
1111111111	1023	1101111000100101

RAM Read and Write

Control inputs:

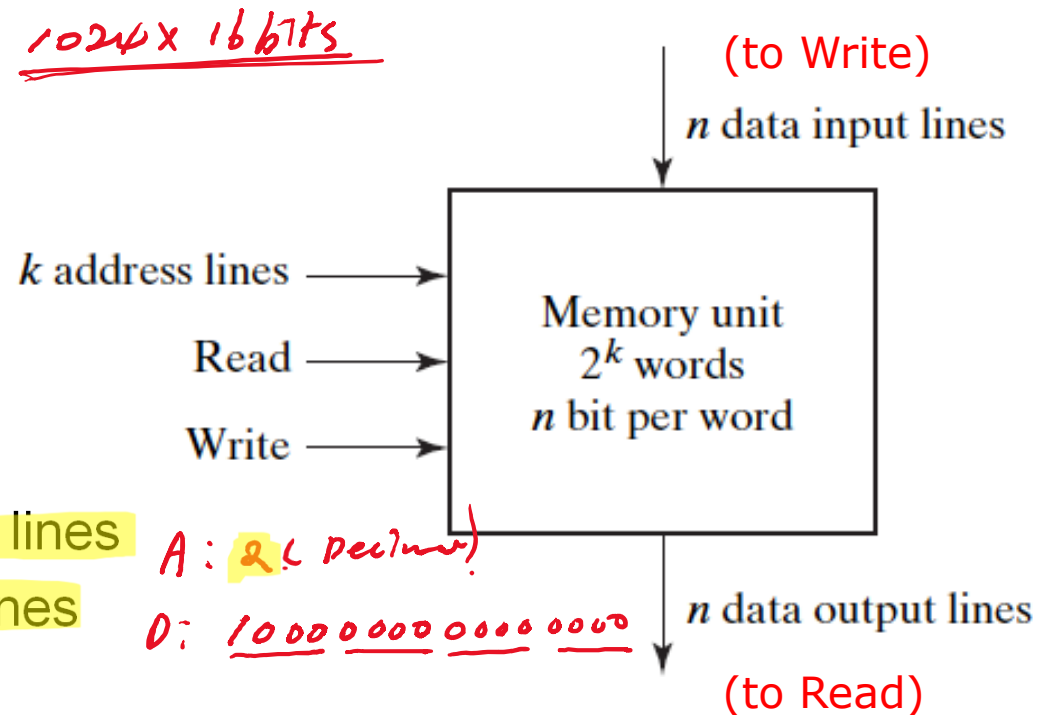
- Address
- Read
- Write

Write operation

1. Apply address to address lines
2. Apply data to data input lines
3. Activate write input

Read operation

1. Apply address to address line
2. Activate read input
3. Read value from data output lines



RAM Read and Write

■ Control inputs on commercial memories

- Memory enable
- Read and write (often read/write)

$$R/\bar{W} = 0; \underline{R} = 0; \bar{W} = 0 \quad (W = 1)$$

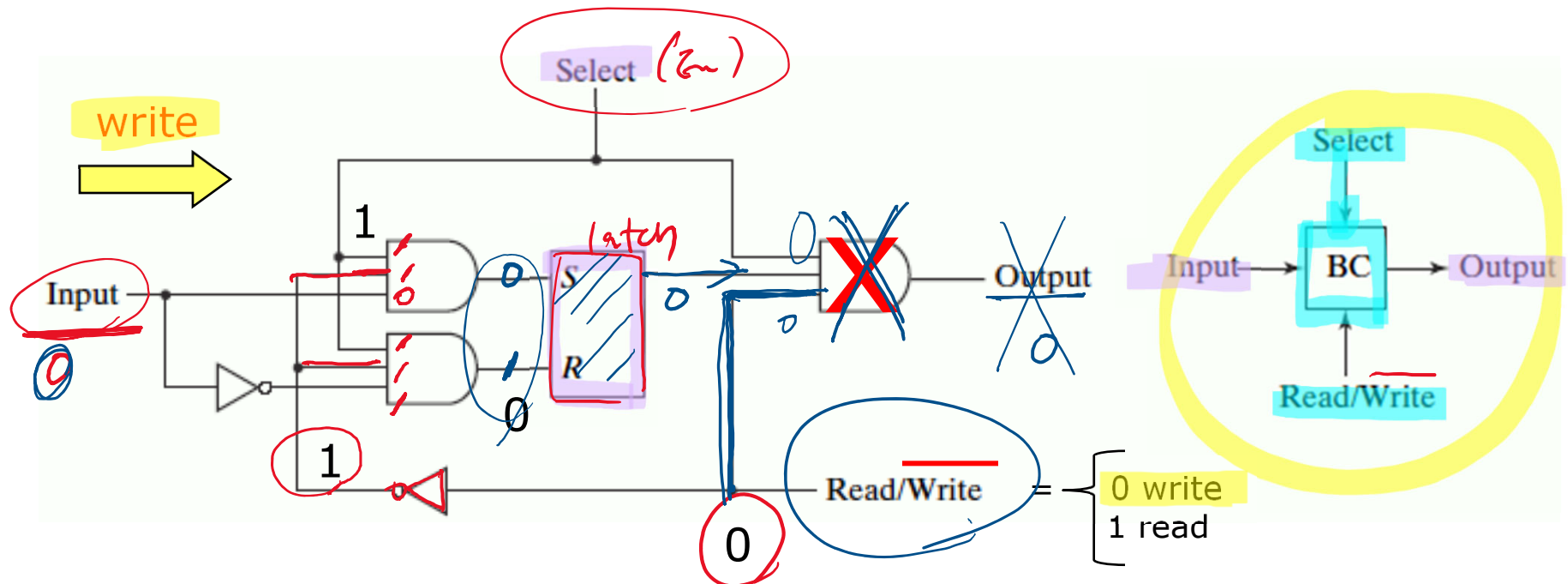
Memory enable	Read / <u>write</u>	Memory operation
0	X	none
1	0	<u>write to selected word</u>
1	<u>1</u>	<u>read from selected word</u>

■ What timing constraints need to be considered?

- Access *time* = time to read a word
- Cycle *time* = time to write a word
- Also: *setup* and *hold time* on address lines

Memory Cell Design

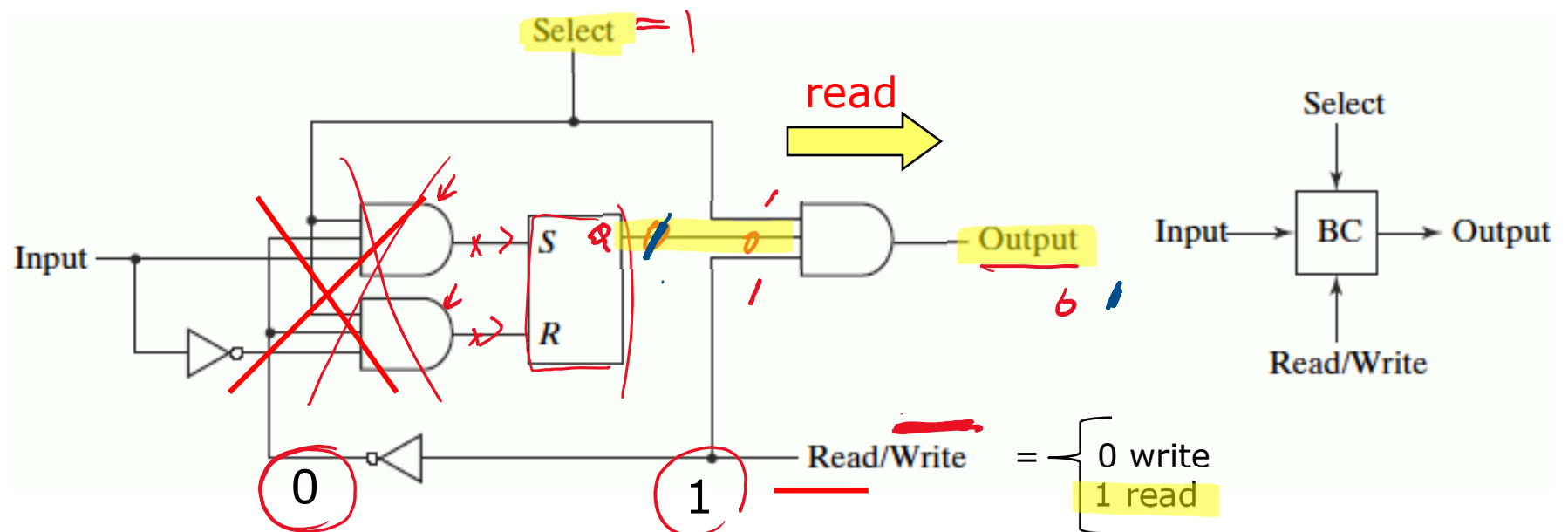
- Binary memory cell implemented with SR latch:



- Note: memory is not clocked

Memory Cell Design

- Binary memory cell implemented with SR latch (nor gate based):

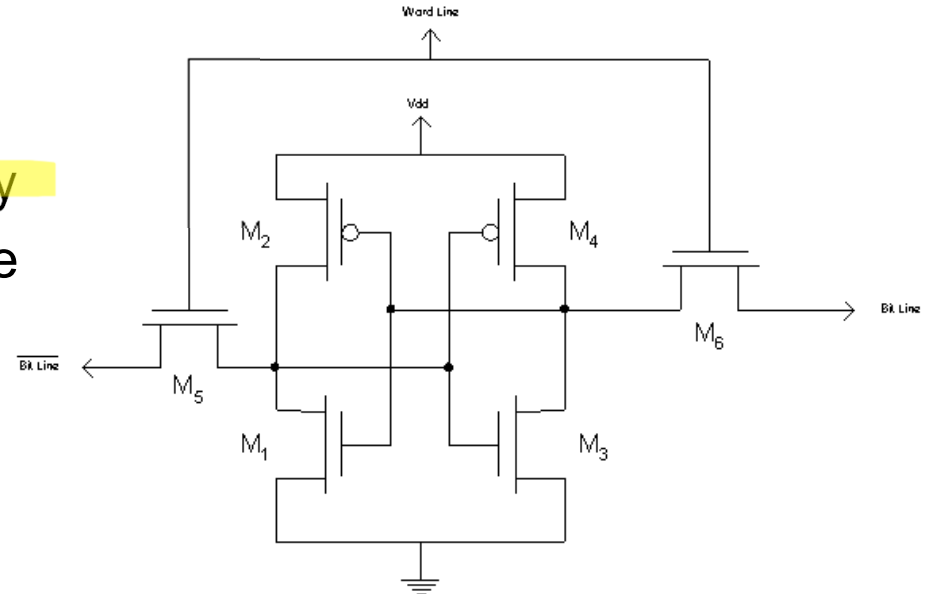


- Note: memory is not clocked

RAM Types

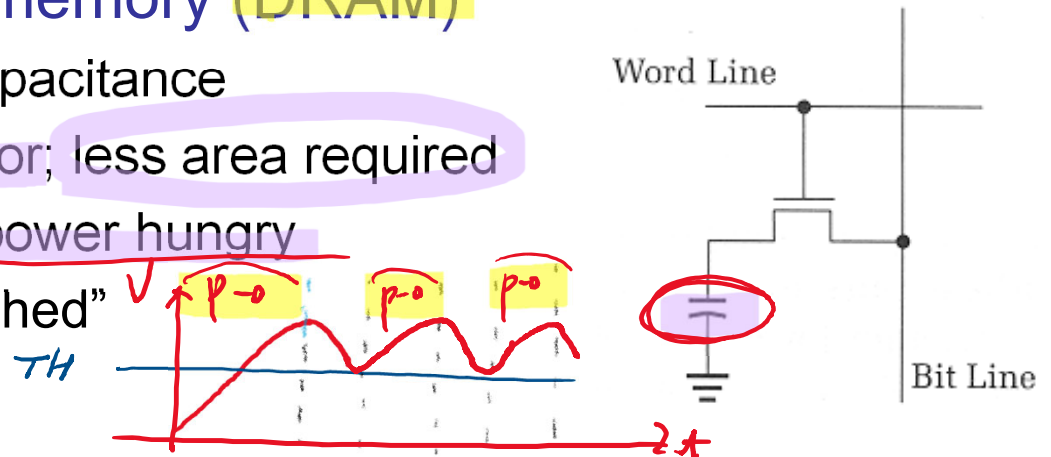
■ Static random access memory (SRAM)

- Operates like a latch
- Implemented with 6 transistors
- Fast operation, but power hungry
- Memory retains information while power is applied



■ Dynamic random access memory (DRAM)

- Data stored as charge in capacitance
- Implemented with 1 transistor; less area required
- Slower operation, but less power hungry
- Memory needs to be "refreshed"

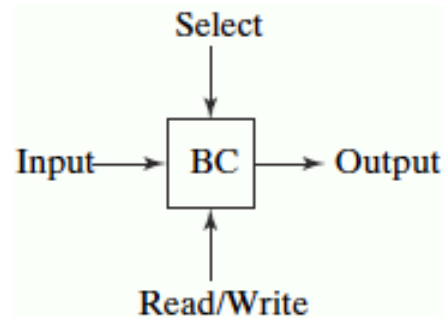


Memory Organization

Internal layout of memory:

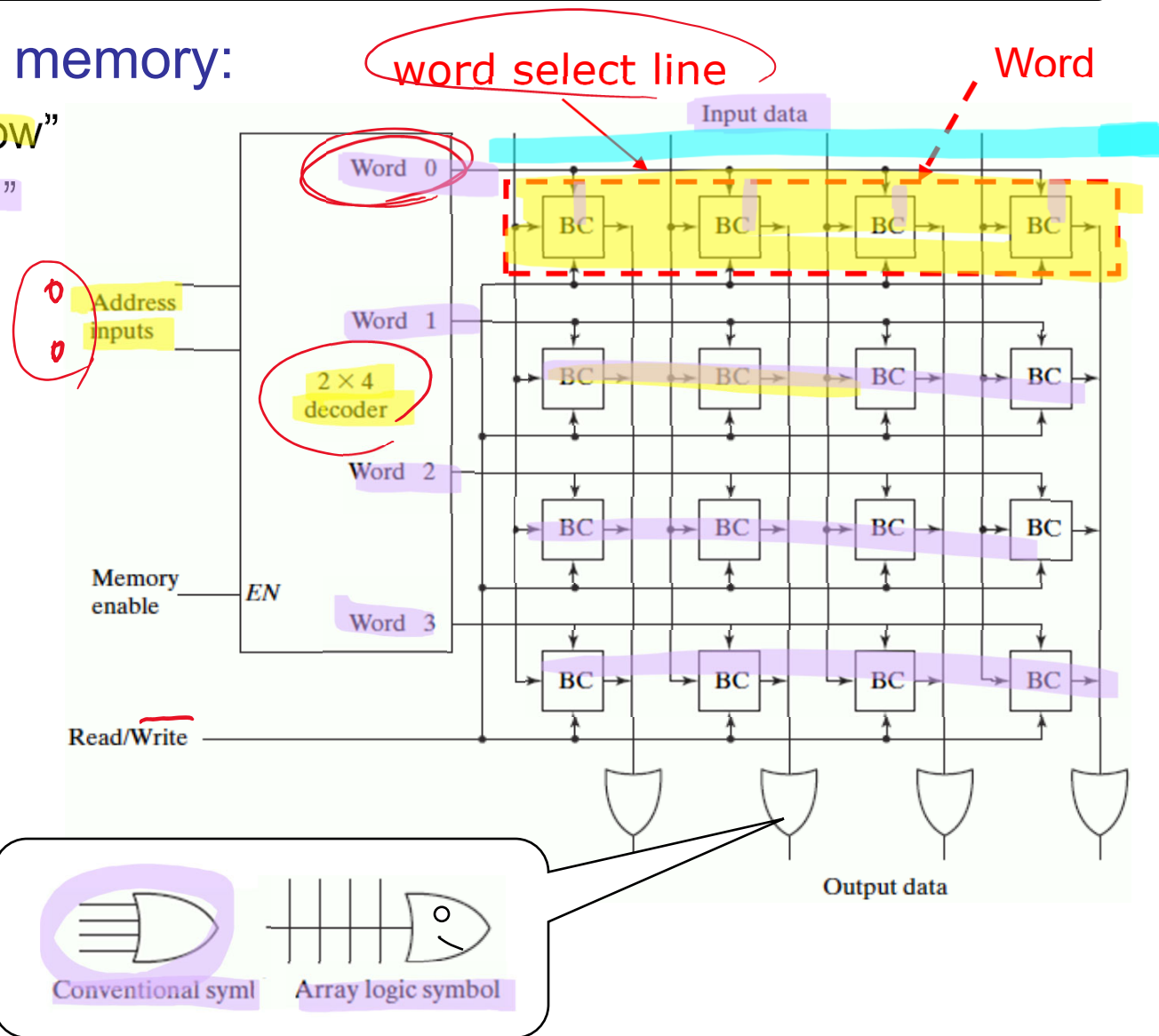
- One word per "row"
- Each "binary cell" stores one bit

Memory cell:



Decoder:

- Selects word



Coincident Decoding – Address Splitting

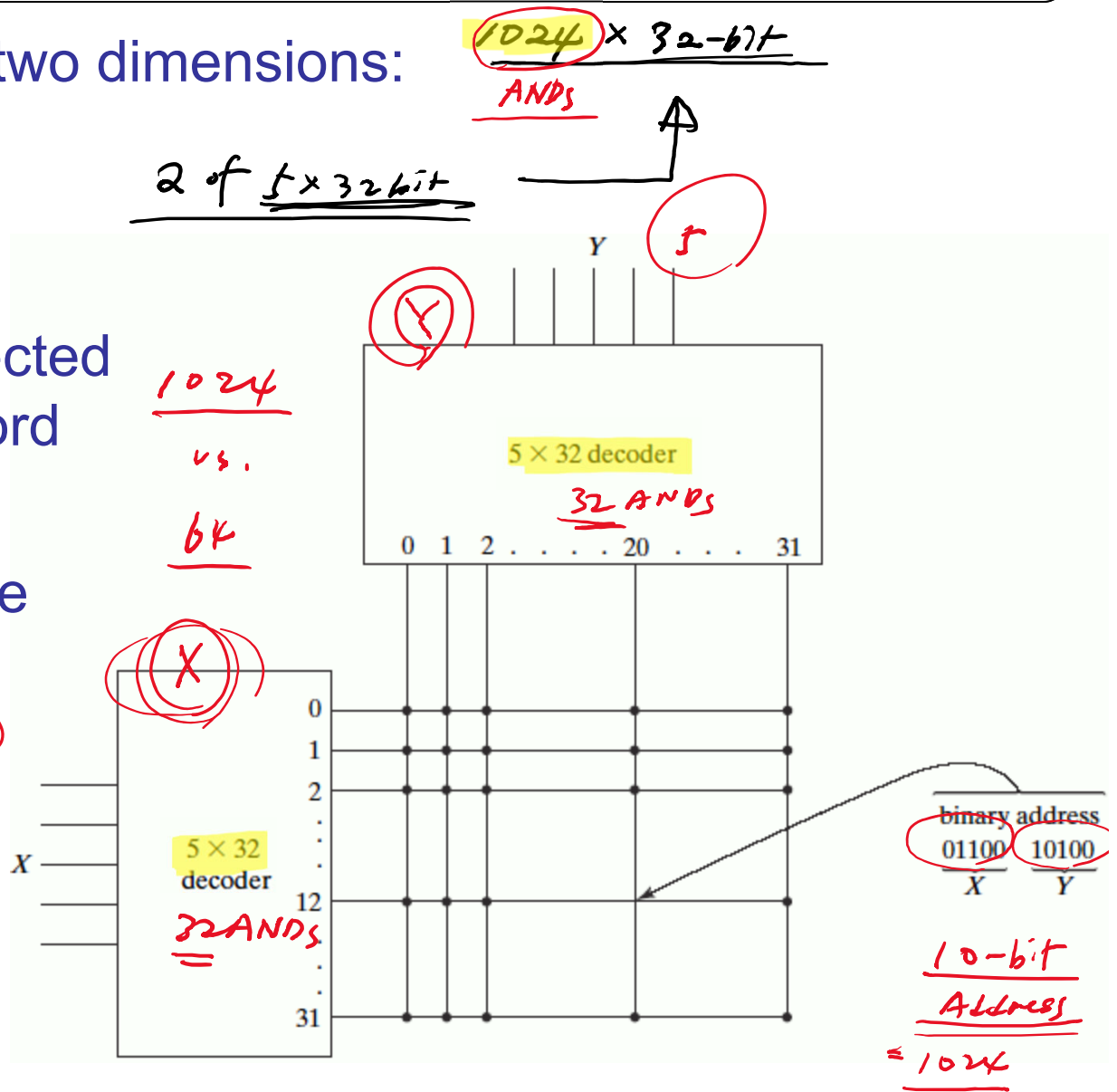
- Split decoders into two dimensions:

- $k/2 \times 2^{k/2}$ decoder in each dimension

- Coincidence of selected lines determines word

- How many gates are required?

- $32 + 32 = 64$ ANDs with 5 inputs each



Address Multiplexing - DRAM

- Number of pins on memory chip impacts cost
 - How can we reduce the number of pins necessary?
- Address multiplexing
 - Address is transmitted in parts
 - Multiplexing in time
- Example: 64k word DRAM
 - Bit-addressable
 - » 2^{16} address space
 - 16 bits of address are split (multiplexed) in time by strobing
 - » CAS: "Column Address Strobe"
 - » RAS: "Row Address Strobe"

